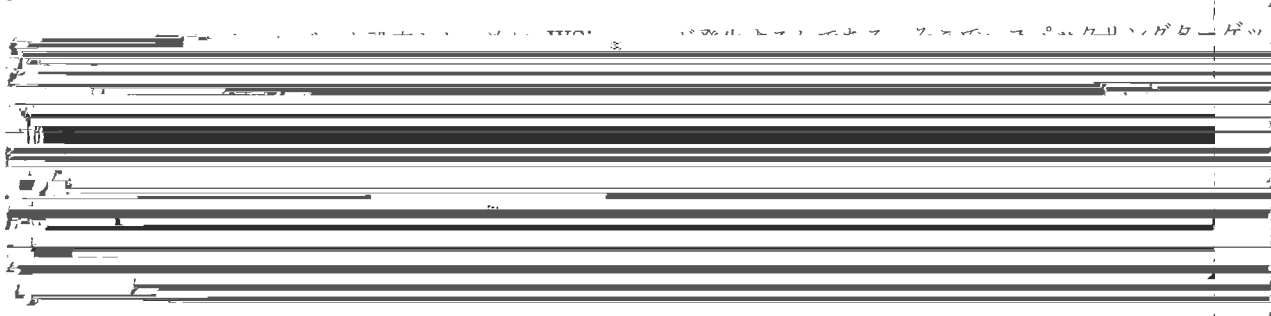


Fig. 1. Schematic of sputtering target.



emission due to an arc at cone on sputtering target.

対値は低抵抗の部分より小さくなる。これにより、高抵

る。このエネルギー低下によってスパッタ率が低い部分

ができ、その部分が

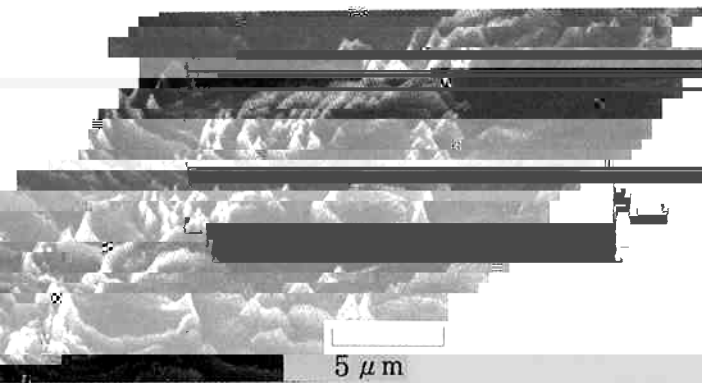
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5 μm

of typical pores formed in

coarse grains of excess Si<sup>4+</sup> Rounded or

(Viewing angle in SEM is 45 deg relative

to the sample's normal).

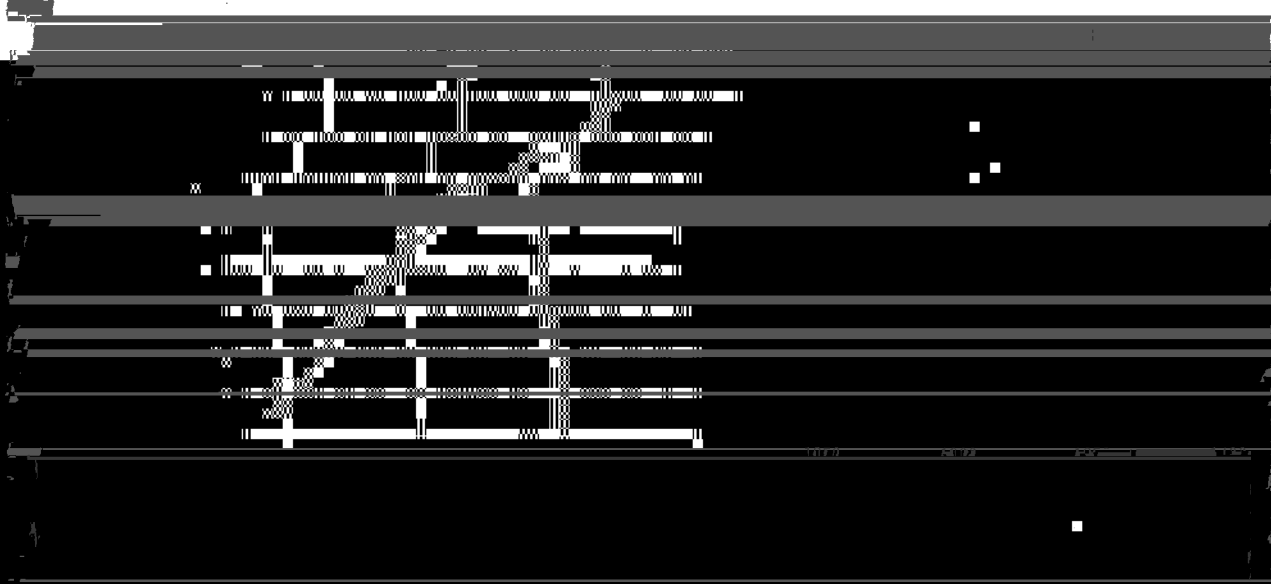
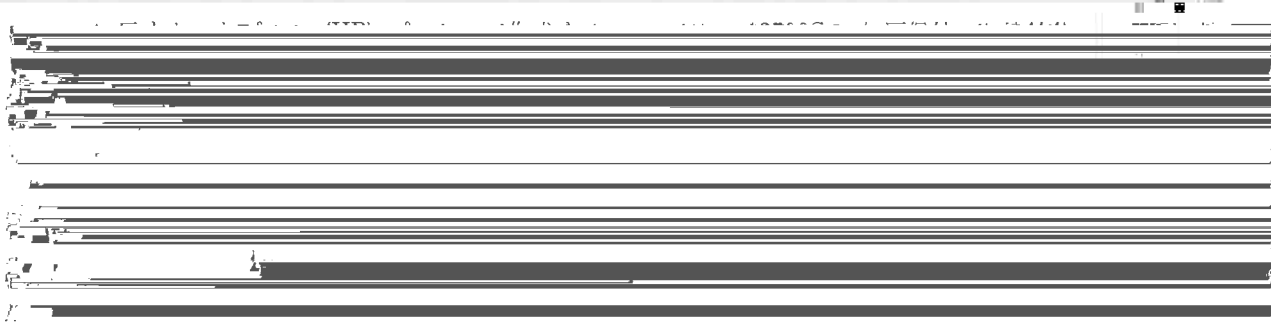
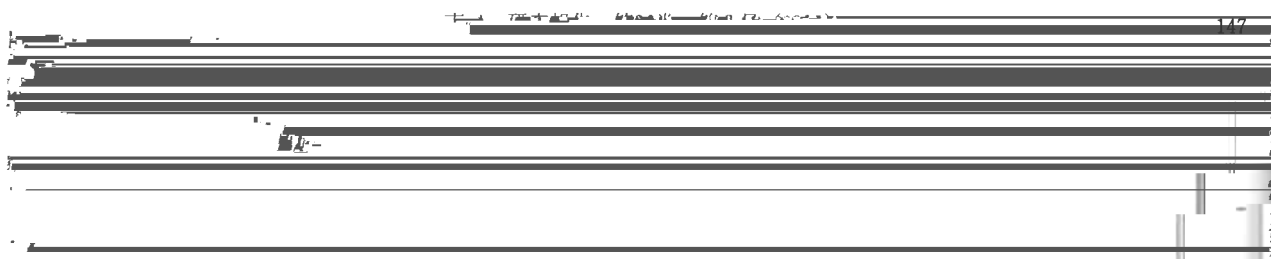


Fig. R. Relation between initial temperature and





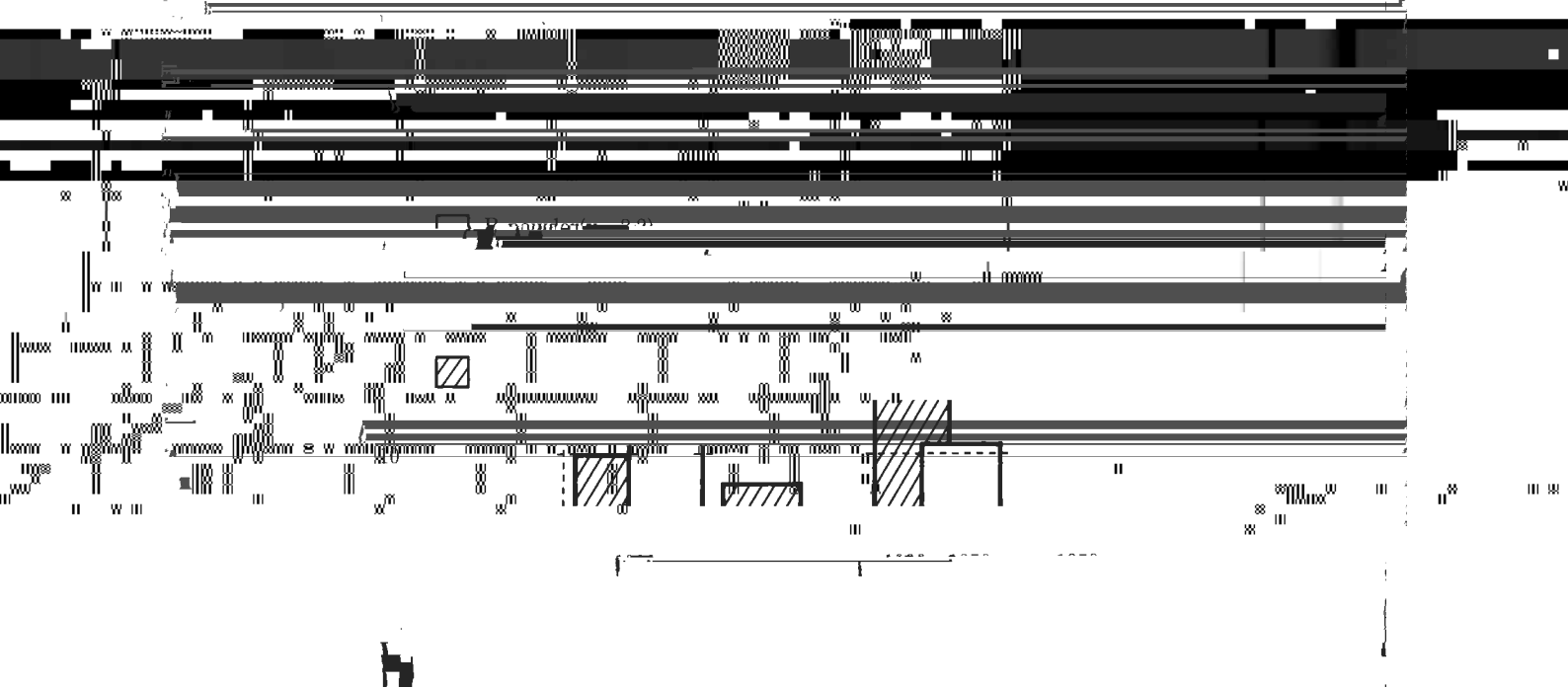
Fig. 9 Microstructure of sintered  $WSi_x$ .

(b) sintering temperature: 1360°C.

1. 实验装置  
 2. 实验结果  
 3. 讨论  
 4. 结论  
 5. 参考文献  
 6. 附录

Cathode type	planer DC magnetron
Input power	0.15 kW
Sputtering gas	Ar
Pressure	0.9 Pa
Substrate temperature	400°C

7. 致谢  
 8. 作者简介  
 9. 收稿日期







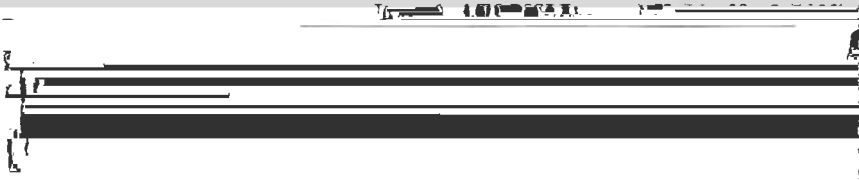
謝 辞

Particle number per  $\phi 2$  inch are

0 1000 2000 3000 4000 5000  
Cone density ( $\text{mm}^{-2}$ )

Fig. 15 Relation between cone density and

た。

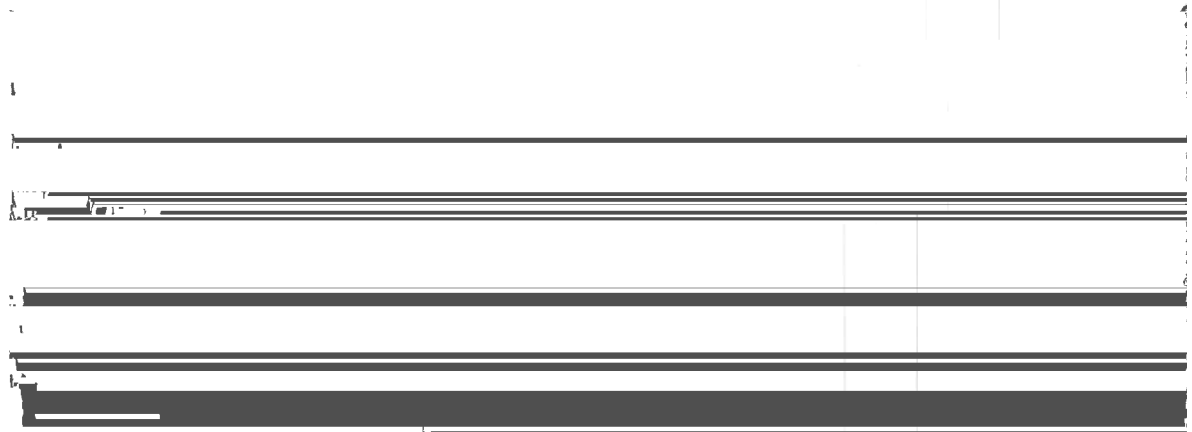


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